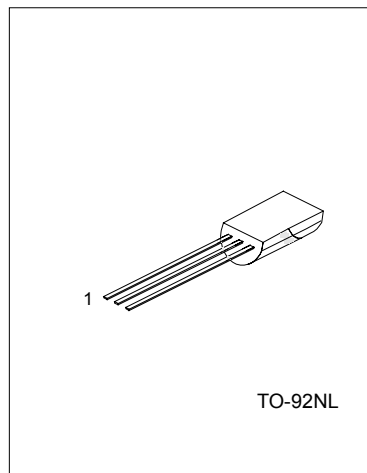


# UTC 2SC2328A NPN EPITAXIAL SILICON TRANSISTOR

## AUDIO POWER AMPLIFIER

### FEATURES

- \*Collector Dissipation  $P_c=1$  W
- \*3 W Output Application
- \*Complement of 2SA928A



1: EMITTER 2: COLLECTOR 3: BASE

### ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CB0</sub>	30	V
Collector-emitter voltage	V <sub>CEO</sub>	30	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector dissipation	P <sub>c</sub>	1	W
Collector current	I <sub>c</sub>	2	A
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV <sub>CB0</sub>	I <sub>c</sub> =100μA, I <sub>E</sub> =0	30			V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>c</sub> =10mA, I <sub>B</sub> =0	30			V
Emitter-base breakdown voltage	BV <sub>EB0</sub>	I <sub>E</sub> =1mA, I <sub>c</sub> =0	5			V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> =30V, I <sub>E</sub> =0			100	nA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>BE</sub> =5V, I <sub>c</sub> =0			100	nA
DC current gain(note)	h <sub>FE</sub>	V <sub>CE</sub> =2V, I <sub>c</sub> =500mA	100		320	
Base-emitter on voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> =2V, I <sub>c</sub> =500mA			1	V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =1.5A, I <sub>B</sub> =0.03A			2	V
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		30		pF
Current gain bandwidth product	f <sub>t</sub>	V <sub>CE</sub> =2V, I <sub>c</sub> =500mA		120		MHz

### CLASSIFICATION OF h<sub>FE</sub>

RANK	O	Y
RANGE	100-200	160-320

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## TYPICAL CHARACTERISTIC CURVES

